PEMD14; PUMD14

NPN/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = open

Rev. 02 — 2 September 2009

Product data sheet

1. Product profile

1.1 General description

NPN/PNP resistor-equipped transistors

Table 1. Product overview

Type number			PNP/PNP complement	NPN/NPN complement
	NXP	JEITA		
PEMD14	SOT666	-	PEMB14	PEMH14
PUMD14	SOT363	SC-88	PUMB14	PUMH14

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place cost

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replacement of general-purpose transistors in digital applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
I _O	output current (DC)		-	-	100	mA
R1	bias resistor 1 (input)		33	47	61	kΩ



2. Pinning information

Table 3. Pinning

Table 3.	rinning		
Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	6 5 4
3	output (collector) TR2		R1
4	GND (emitter) TR2		TR2
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	R1
			1 2 3
			006222260

3. Ordering information

Table 4. Ordering information

Type number	Package				
	Name	Description	Version		
PEMD14	-	plastic surface mounted package; 6 leads	SOT666		
PUMD14	SC-88	plastic surface mounted package; 6 leads	SOT363		

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PEMD14	5B
PUMD14	T2*

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor; for the PNP transistor v	with negative polar	ity		
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	5	V
Io	output current (DC)		-	100	mA
I _{CM}	peak collector current		-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	SOT363		[1] -	200	mW
	SOT666		[1] [2] _	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
Per device)				
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	SOT363		<u>[1]</u> -	300	mW
	SOT666		[1] [2] _	300	mW

^[1] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7. Thermal characteristics

Parameter	Conditions	Min	Тур	Max	Unit
stor					
thermal resistance from junction to ambient	$T_{amb} \le 25 ^{\circ}C$				
SOT363		<u>[1]</u> -	-	625	K/W
SOT666		[1] [2]	-	625	K/W
•					
thermal resistance from junction to ambient	$T_{amb} \le 25 ^{\circ}C$				
SOT363		<u>[1]</u> -	-	416	K/W
SOT666		[1] [2]	-	416	K/W
	thermal resistance from junction to ambient SOT363 SOT666 thermal resistance from junction to ambient SOT363	thermal resistance from junction to ambient $SOT363$ $SOT666$ thermal resistance from junction to ambient $T_{amb} \le 25 ^{\circ}\text{C}$	thermal resistance from junction to ambient $ \begin{array}{c} \text{T}_{amb} \leq 25 \text{ °C} \\ \text{junction to ambient} \\ \text{SOT363} & \boxed{1} - \\ \text{SOT666} & \boxed{1} \boxed{2} - \\ \\ \text{thermal resistance from junction to ambient} \\ \text{SOT363} & \boxed{1} - \\ \\ \end{array} $	thermal resistance from junction to ambient $ \begin{array}{c} \text{T}_{amb} \leq 25 \text{ °C} \\ \text{junction to ambient} \\ \hline \text{SOT363} & \boxed{11} \\ \hline \text{SOT666} & \boxed{11} \boxed{2} \\ \hline \\ \text{thermal resistance from junction to ambient} \\ \hline \text{SOT363} & \boxed{11} \\ \hline \end{array} $	thermal resistance from junction to ambient $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

^[1] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

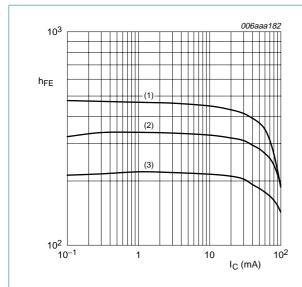
^[2] Reflow soldering is the only recommended soldering method.

Characteristics

Table 8. **Characteristics**

T_{amb} = 25 °C unless otherwise specified

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor; for the PNP transis	tor with negative polarity				
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO} collector-er	collector-emitter	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	1	μΑ
	cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 1 \text{ mA}$	100	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
R1	bias resistor 1 (input)		33	47	61	kΩ
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz				
	TR1 (NPN)		-	-	2.5	pF
	TR2 (PNP)		-	-	3	pF



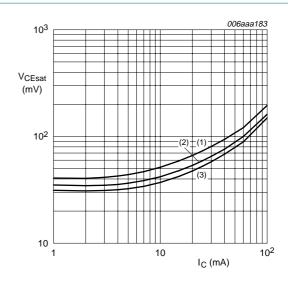
 $V_{CE} = 5 V$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \,^{\circ}C$$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig 1. TR1 (NPN): DC current gain as a function of collector current; typical values



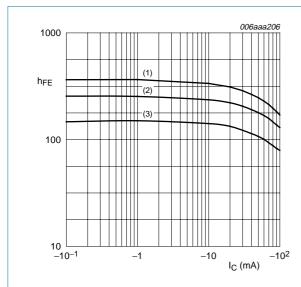
 $I_{\rm C}/I_{\rm B} = 20$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \,^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 2. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



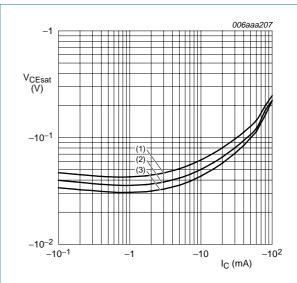
 $V_{CE} = -5 \text{ V}$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \,^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 3. TR2 (PNP): DC current gain as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B}=20$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \,^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 4. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

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8. Package outline

Plastic surface-mounted package; 6 leads

SOT363

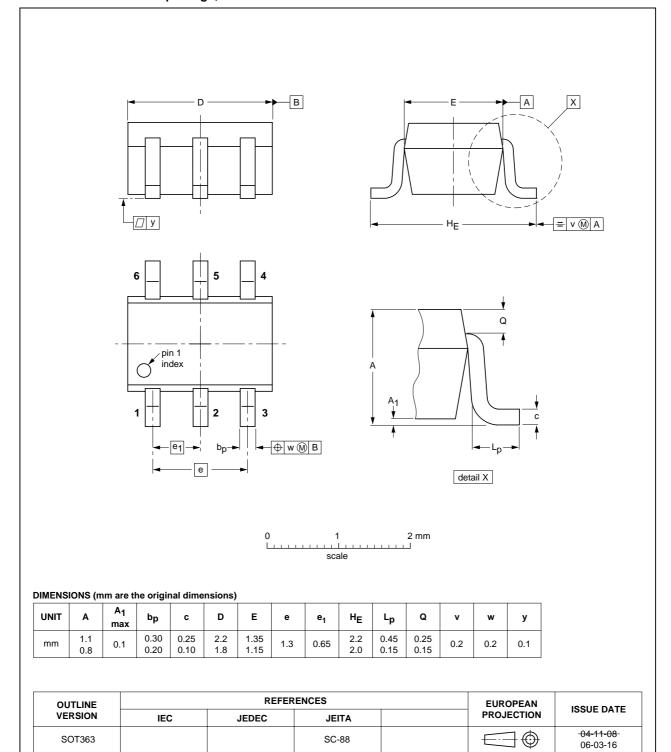


Fig 5. Package outline SOT363 (SC-88)

Plastic surface-mounted package; 6 leads

SOT666

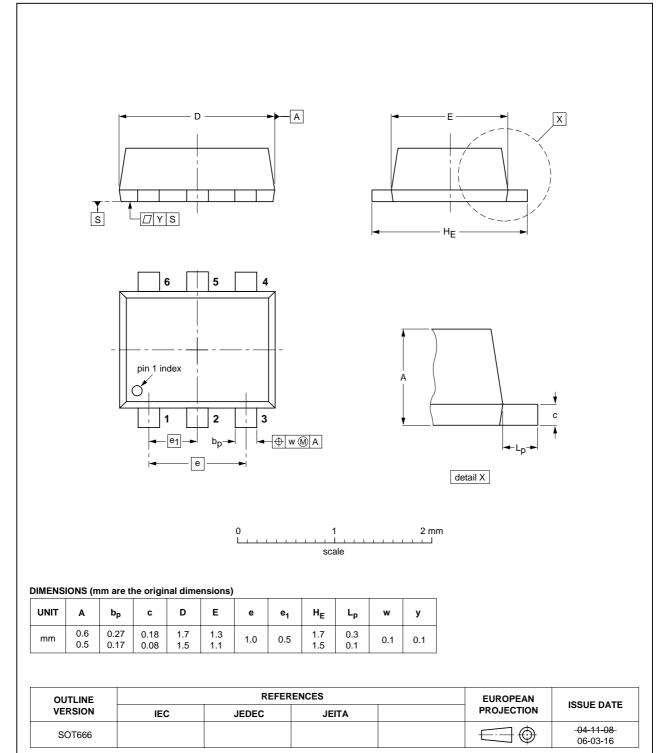


Fig 6. Package outline SOT666

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9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description	Packing o	uantity	
			3000	4000	10000
PEMD14	SOT666	4 mm pitch, 8 mm tape and reel	-	-115	-
PUMD14	SOT363	4 mm pitch, 8 mm tape and reel; T1	·115	-	-135
PUMD14	SOT363	4 mm pitch, 8 mm tape and reel; T2	125	-	-165

^[1] For further information and the availability of packing methods, see Section 12.

^[2] T1: normal taping

^[3] T2: reverse taping

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NPN/PNP resistor-equipped transistors; R1 = 47 kΩ, R2 = open

10. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMD14_PUMD14_2	20090902	Product data sheet	-	PEMD14_PUMD14_1
Modifications:	 This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. 			
	Figure 5 "Page	ckage outline SOT363 (SC	-88)": updated	
	Figure 6 "Pad	ckage outline SOT666": up	dated	
PEMD14_PUMD14_1	20050114	Product data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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